

ABSTRACTDoping of source-drain contacts

A method for forming an electronic device on a substrate, the device including a first electrically conductive region, a second electrically conductive region spaced from the first electrically conductive region and a region of a semiconductor material between the first and second electrically conductive regions and in contact with the first electrically conductive region, the method comprising doping an interfacial zone comprising least part of the periphery of the semiconductor material at the interface between the semiconductor material and the first electrically conductive region by means of a dopant contained in the first conductive material and capable of doping the semiconducting material so as to thereby enhance the conductivity of the interfacial zone.

Figure 2